

**P- Channel 60-V (D-S) MOSFET**

**GENERAL DESCRIPTION**

The ME60P06T is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance.

**FEATURES**

- $R_{DS(ON)} \leq 16.5m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 20.5m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

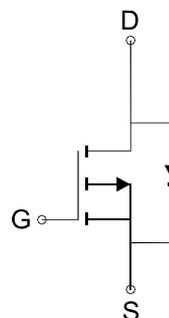
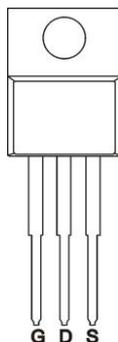
**APPLICATIONS**

- Power Management in Note book
- DC/DC Converter
- Load Switch
- LCD Display inverter

**PIN CONFIGURATION**

(TO-220)

Top View



P-Channel MOSFET

Ordering Information: ME60P06T (Pb-free)

ME60P06T-G (Green product-Halogen free )

**Absolute Maximum Ratings (Tc=25°C Unless Otherwise Noted)**

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current*	$I_D$	Tc=25°C	-55.3
		Tc=70°C	-46.3
Pulsed Drain Current	$I_{DM}$	-221	A
Maximum Power Dissipation*	$P_D$	Tc=25°C	90.9
		Tc=70°C	63.6
Operating Junction Temperature	$T_J$	-55 to 175	°C
Thermal Resistance-Junction to Case*	$R_{\theta JC}$	1.65	°C/W

\*The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper



**P- Channel 60-V (D-S) MOSFET**
**Electrical Characteristics (T<sub>c</sub> =25°C Unless Otherwise Specified)**

Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250 μA	-60			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250 μA	-1		-3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V			-1	μA
R <sub>DS(ON)</sub>	Drain-Source On-State Resistance <sup>a</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> = -30A		13	16.5	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> = -20A		15	20.5	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-30A, V <sub>GS</sub> =0V		-1.0	-1.5	V
<b>DYNAMIC</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-50A		98.6		nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =-30V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-50A		50.1		
Q <sub>gs</sub>	Gate-Source Charge			15.9		
Q <sub>gd</sub>	Gate-Drain Charge			25.2		
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, F=1MHz		4480		pF
C <sub>oss</sub>	Output Capacitance			427		
C <sub>rss</sub>	Reverse Transfer Capacitance			355		
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =-30V, R <sub>L</sub> =30Ω V <sub>GEN</sub> =-10V, R <sub>G</sub> =6Ω		50.7		ns
t <sub>r</sub>	Turn-On Rise Time			18.1		
t <sub>d(off)</sub>	Turn-Off Delay Time			221		
t <sub>f</sub>	Turn-Off Fall Time			60.1		

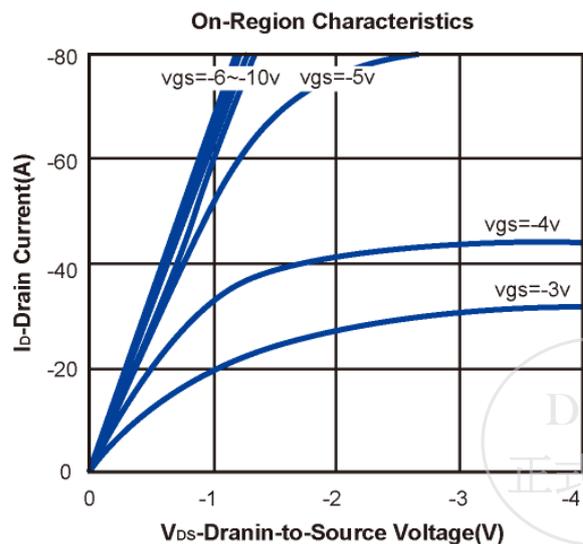
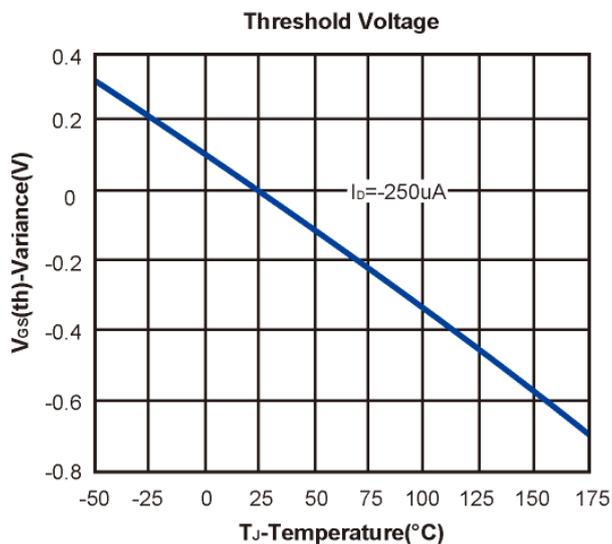
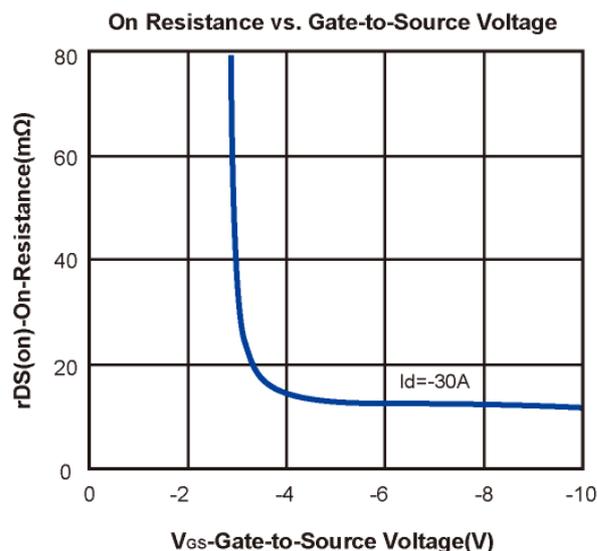
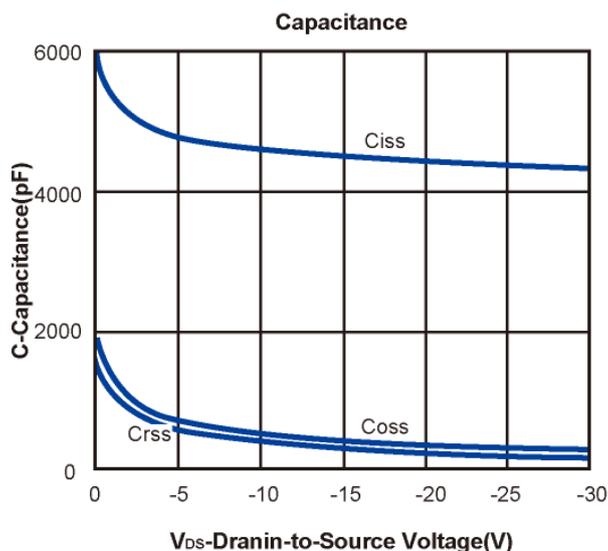
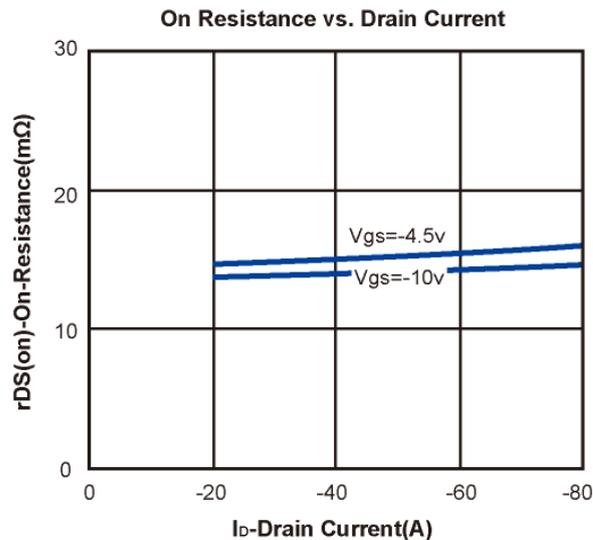
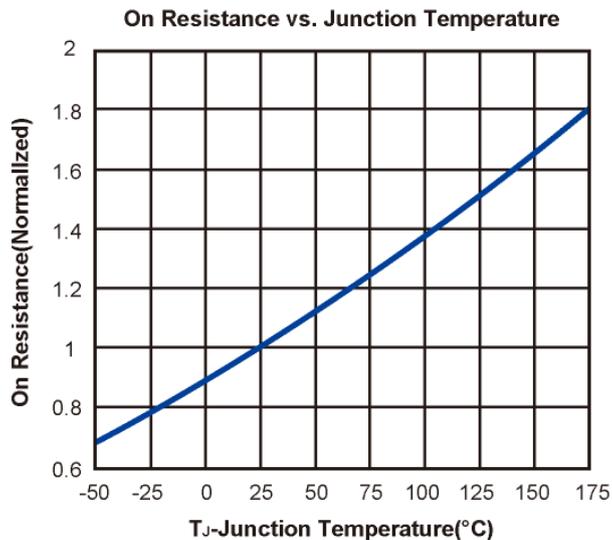
Notes:a. Pulse test; pulse width ≤ 300us, duty cycle ≤ 2%

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.



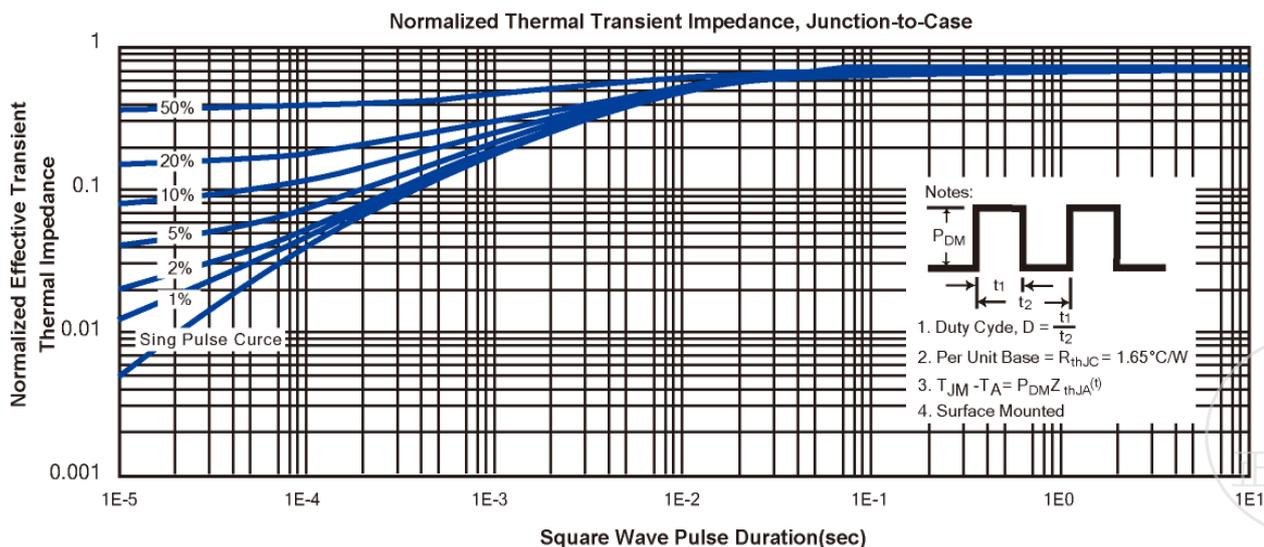
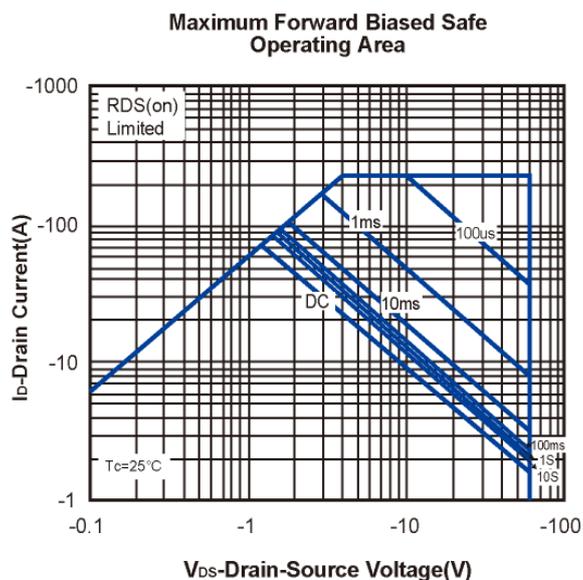
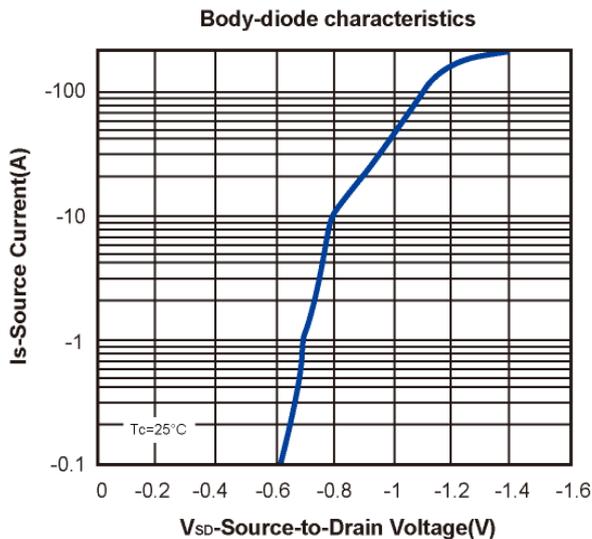
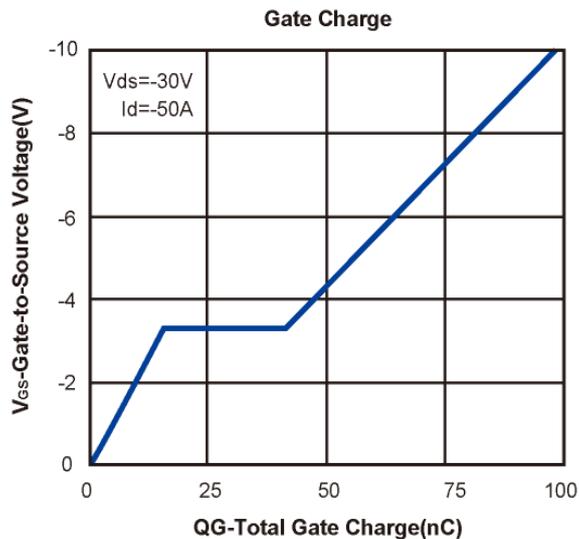
**P- Channel 60-V (D-S) MOSFET**

Typical Characteristics (T<sub>J</sub> =25°C Noted)

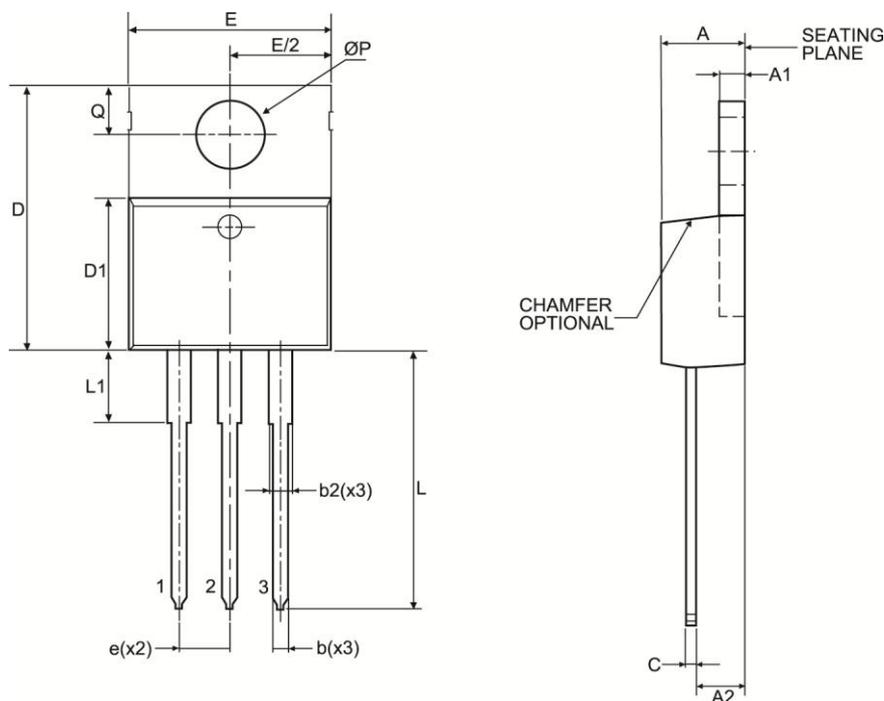


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**TO-220 Package Outline**



Symbol	MILLIMETERS (mm)	
	MIN	MAX
A	3.50	4.90
A1	1.00	1.40
A2	2.00	3.00
b	0.70	1.40
c	0.35	0.65
D	14.00	16.50
D1	8.30	9.50
E	9.60	10.70
e	2.54 BSC	
L	12.50	15.00
ØP	3.60 TYP	
Q	2.50	3.10
b2	1.10	1.80
L1	2.40	3.20



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